

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED MESA TYPE

2SD2553

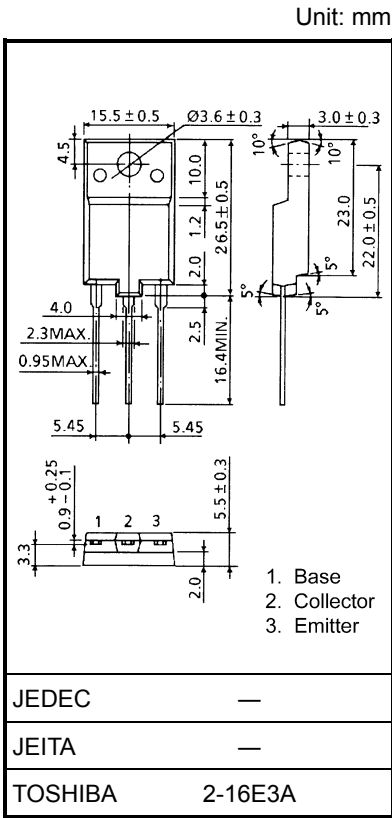
HORIZONTAL DEFLECTION OUTPUT FOR HIGH  
RESOLUTION DISPLAY, COLOR TV

HIGH SPEED SWITCHING APPLICATIONS

- High Voltage :  $V_{CBO} = 1700\text{ V}$
- Low Saturation Voltage :  $V_{CE(sat)} = 5\text{ V (Max.)}$
- High Speed :  $t_f = 0.3\text{ }\mu\text{s (Typ.)}$
- Built-in Damper Type
- Collector Metal (Fin) is Fully Covered with Mold Resin.

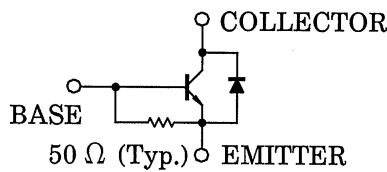
MAXIMUM RATINGS ( $T_c = 25^\circ\text{C}$ )

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		$V_{CBO}$	1700	V
Collector-Emitter Voltage		$V_{CEO}$	600	V
Emitter-Base Voltage		$V_{EBO}$	5	V
Collector Current	DC	$I_C$	8	A
	Pulse	$I_{CP}$	16	
Base Current		$I_B$	4	A
Collector Power Dissipation		$P_C$	50	W
Junction Temperature		$T_j$	150	$^\circ\text{C}$
Storage Temperature Range		$T_{stg}$	-55~150	$^\circ\text{C}$



Weight: 5.5 g (typ.)

EQUIVALENT CIRCUIT



CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN	TYP.	MAX	UNIT
Collector Cut-off Current		$I_{CBO}$	$V_{CB} = 1700 \text{ V}, I_E = 0$	—	—	1	mA
Emitter Cut-off Current		$I_{EBO}$	$V_{EB} = 5 \text{ V}, I_C = 0$	66	—	200	mA
Emitter–Base Breakdown Voltage		$V_{(BR) EBO}$	$I_C = 400 \text{ mA}, I_C = 0$	5	—	—	V
DC Current Gain		$h_{FE} (1)$	$V_{CE} = 5 \text{ V}, I_C = 1 \text{ A}$	8	—	28	—
		$h_{FE} (2)$	$V_{CE} = 5 \text{ V}, I_C = 6 \text{ A}$	5	—	9	
Collector–Emitter Saturation Voltage		$V_{CE (sat)}$	$I_C = 6 \text{ A}, I_B = 1.2 \text{ A}$	—	—	5	V
Base–Emitter Saturation Voltage		$V_{BE (sat)}$	$I_C = 6 \text{ A}, I_B = 1.2 \text{ A}$	—	0.9	1.2	V
Forward Voltage (Damper Diode)		$V_F$	$I_F = 8 \text{ A}$	—	1.6	2.0	V
Transition Frequency		$f_T$	$V_{CE} = 10 \text{ V}, I_C = 0.1 \text{ A}$	—	2	—	MHz
Collector Output Capacitance		$C_{ob}$	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$	—	155	—	pF
Switching Time (Fig.1)	Storage Time	$t_{stg}$	$I_{CP} = 6 \text{ A}, I_{B1} (end) = 1.5 \text{ A}$	—	9	12	$\mu s$
	Fall Time	$t_f$	$f_H = 15.75 \text{ kHz}$	—	0.3	0.7	

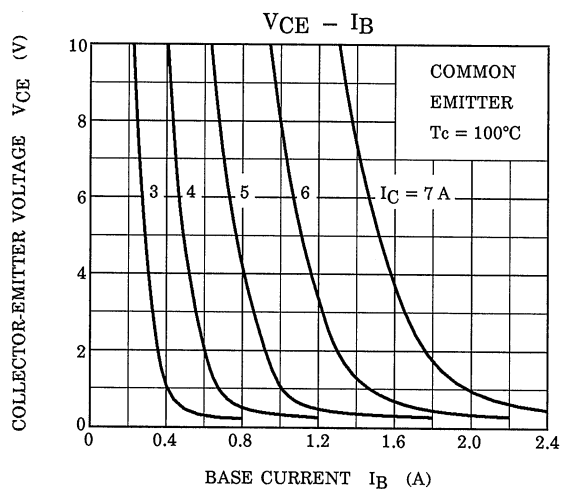
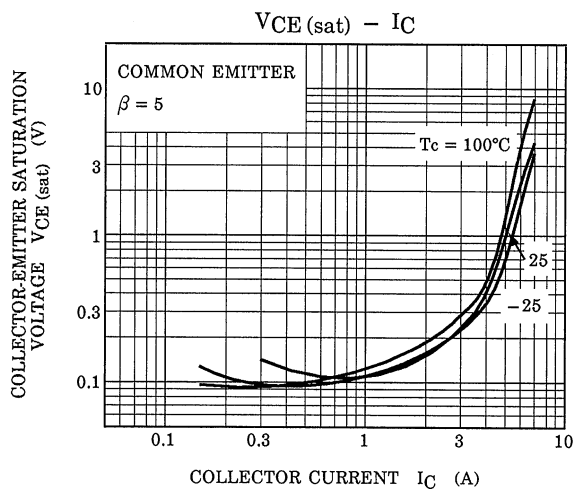
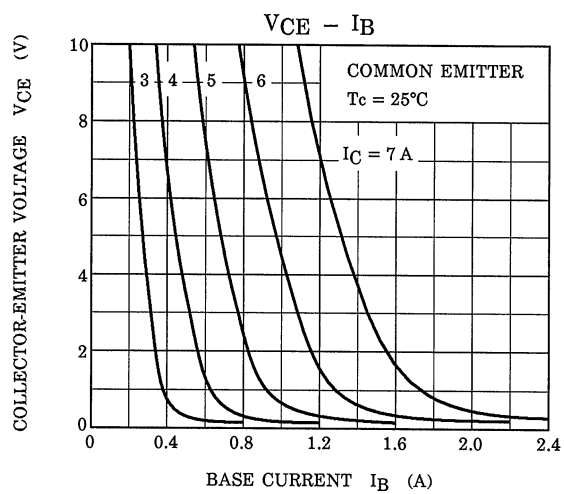
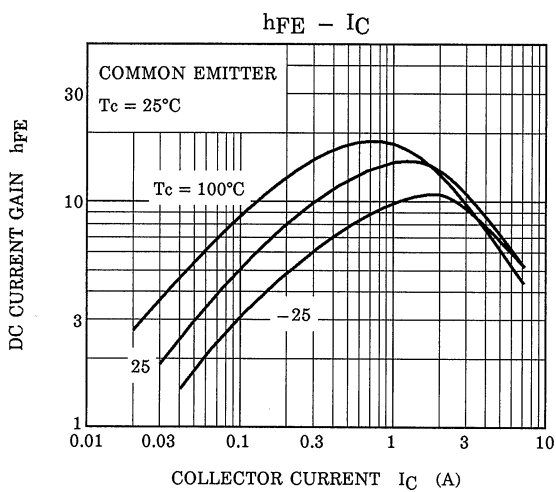
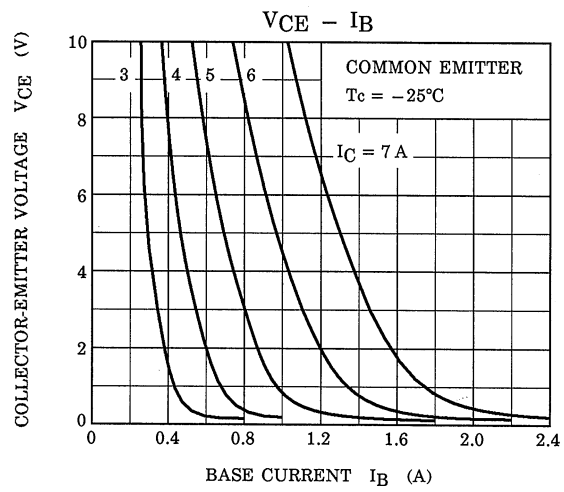
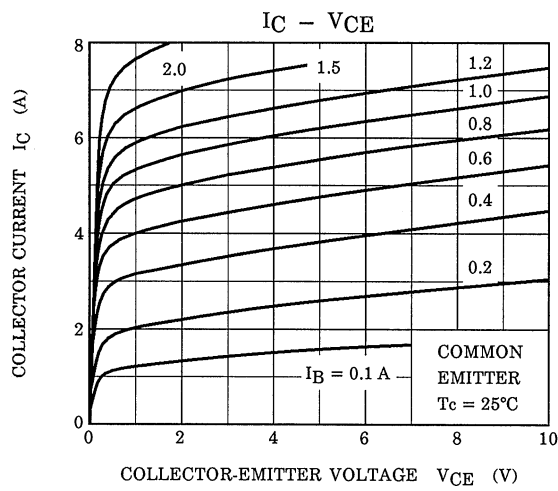
The diagram shows a 2SC2482 transistor inverter circuit. The input is a square wave with a pulse width of  $25\ \mu\text{s}$  and a period of  $63.5\ \mu\text{s}$ . The circuit includes a  $3\text{ k}\Omega$  base resistor, a  $100\ \mu\text{F}$  capacitor, and a  $250\ \Omega$  resistor connected to  $V_{DD}$ . The base is also connected to a  $10\ \mu\text{H}$  inductor and a  $100\ \mu\text{F}$  capacitor. The collector is connected to a  $1\text{ M}\Omega$  resistor and a  $0.1\ \mu\text{F}$  capacitor. The emitter is connected to a  $0.018\ \mu\text{F}$  capacitor and a  $2.0\ \mu\text{F}$  capacitor. The output is taken from the collector, which is also connected to a  $10\text{ mH}$  inductor and a  $0.52\text{ mH}$  capacitor. The output waveform shows a base current  $I_B$  and a collector current  $I_C$  with a 90% rise time  $t_{stg}$  and a 10% fall time  $t_f$ .

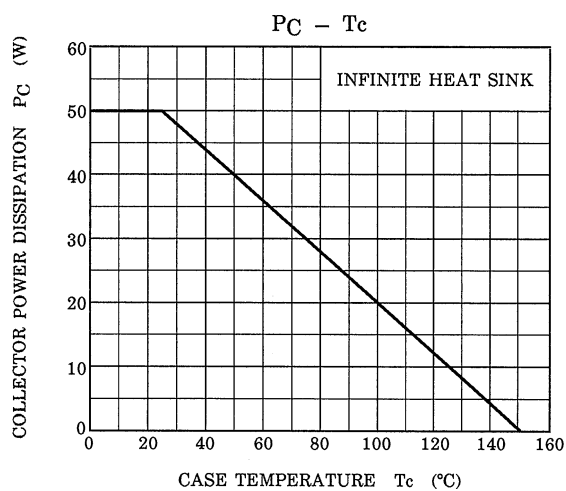
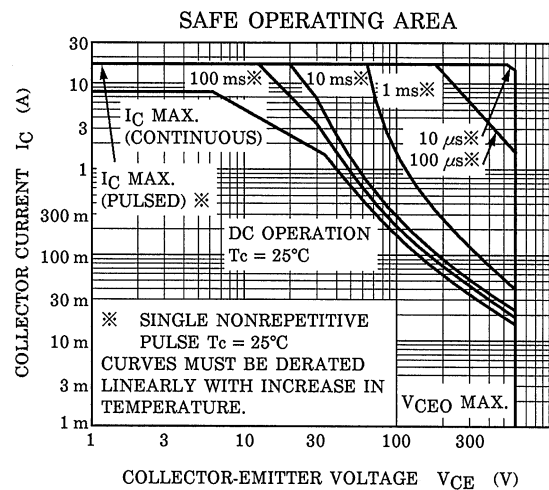
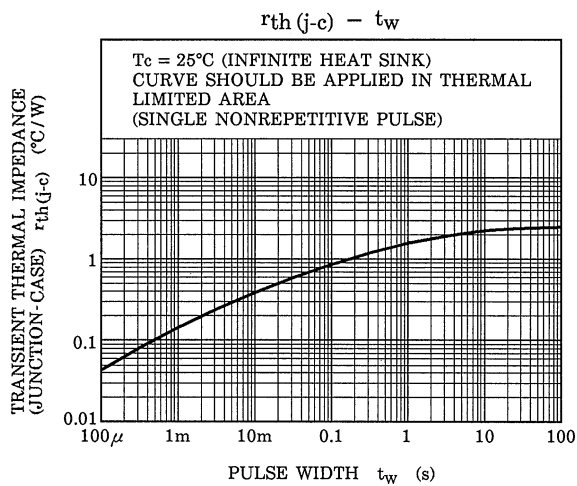
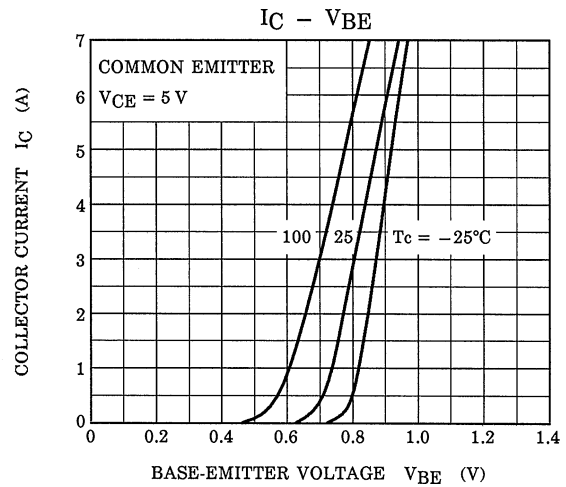
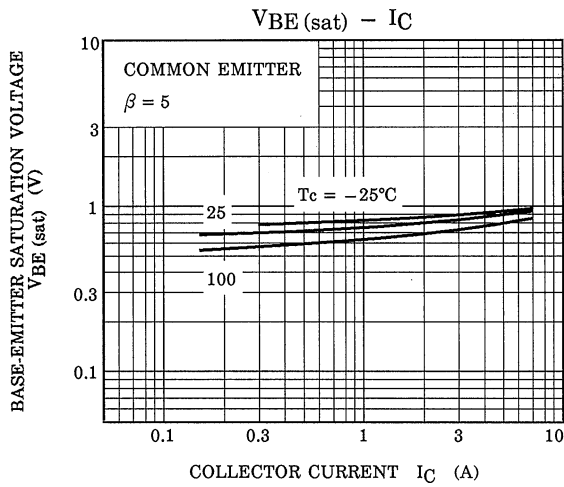
Base Current Gradient

$$\frac{dI_B}{dt} = \frac{I_{B1} + I_{B2}}{t_{stg}} \text{ (A / } \mu\text{s)}$$

Collector Current

Timing waveforms for the base current  $I_B$  and collector current  $I_C$  are shown. The base current waveform is a trapezoid with a peak value  $I_{B1}$  and a valley value  $I_{B2}$ . The collector current waveform is a trapezoid with a peak value  $I_{CP}$  and a valley value  $I_{CB}$ . The rise time  $t_{stg}$  is defined as the time for the base current to rise from 10% to 90% of its peak value. The fall time  $t_f$  is defined as the time for the collector current to fall from 90% to 10% of its peak value.





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